

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Sheldon Aronowitz and)
Vladimir Zubkov)
)
Filed: Herewith)
) Group Art Unit: Unknown
Serial Number: Divisional of 09/792,691)
) Examiner: Unknown
Title: "A Low Dielectric Constant Fluorine and)
Carbon-Containing Silicon Oxide Dielectric)
Material Characterized by Improved Resistance)
to Oxidation")

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.56

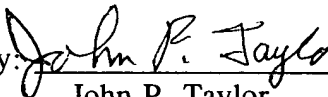
Honorable Commissioner of Patents
and Trademarks
Washington, D.C. 20231

August 29, 2003

Sir:

Pursuant to 37 CFR 1.56, 1.97, and 1.98, Applicants submit the attached form PTO-1449 (modified). This application is a 37 C.F.R. 1.53(b) continuation application of Serial No. 09/792,691. Since all of the documents listed on the enclosed form PTO-1449 (modified) were previously cited to or by the USPTO in the prior application, under the provisions of 37 C.F.R. 1.98(d), copies of the listed documents are not enclosed.

Respectfully submitted,

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FORM PTO-1449 (Modified)
U.S. Department of Commerce, Patent and Trademark Office

Docket No.

Serial No.

00-643/1D

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

Applicants

Sheldon Aronowitz et al.

Filing Date
HerewithGroup
Unknown

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,874,367	2/23/99	Dobson	438	787	
	AB	6,028,015	2/22/00	Wang et al.	438	789	3/29/99
	AC	6,114,259	9/5/00	Sukharev et al.	438	789	7/27/99
	AD	6,147,012	11/14/00	Sukharev et al.	438	787	11/12/99
	AE	6,043,167	3/28/00	Lee et al.	438	789	10/10/97
	AF	5,314,845	5/24/94	Lee et al.	437	238	2/2/90
	AG	5,915,203	6/22/99	Sengupta et al.	438	669	6/10/97
	AH	6,365,528	4/2/02	Sukharev et al.	438	778	6/7/00
	AI	5,571,571	11/5/96	Musaka et al.	427	574	6/14/94
	AJ	6,303,047	10/16/01	Aronowitz et al.	252	1	3/22/99
	AK	6,511,925	1/28/03	Aronowitz et al.	438	788	10/19/01

Foreign Patent Documents

Translation

		Document Number	Date	Country	Class	Subclass	Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AR	Bothra, S., et al., "Integration of 0.25 μ m Three and Five Level Interconnect System for High Performance ASIC", <u>1997 Proceedings Fourteenth International VMIC Conference</u> , Santa Clara, CA, June 10-12, 1997, pp.43-48.
	AS	Dobson, C.D., et al., "Advanced SiO ₂ Planarization Using Silane and H ₂ O ₂ ", <u>Semiconductor International</u> , December 1994, pp. 85-88.
	AT	McClatchie, S., et al., "Low Dielectric Constant Oxide Films Deposited Using CVD Techniques", <u>1998 Proceedings Fourth International DUMIC Conference</u> , February 16-17, 1998, pp. 311-318.

Examiner

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	BA	6,066,574	5/23/00	You et al.	438	781	11/6/98
	BB	6,051,477	4/18/00	Nam	438	404	10/22/96
	BC	6,025,263	2/15/00	Tsai et al.	438	624	9/11/97
	BD	5,939,763	8/17/99	Hao et al.	257	411	9/5/96
	BE	5,864,172	1/26/99	Kapoor et al.	257	634	8/13/96
	BF	5,688,724	11/18/97	Yoon et al.	437	235	12/23/94
	BG	5,470,801	11/28/95	Kapoor et al.	437	238	6/28/93
	BH	5,364,800	11/15/94	Joyner	437	28	6/24/93
	BI	4,771,328	9/13/88	Malaviya et al.	357	49	11/24/86
	BJ	3,652,331	3/28/72	Yamazaki	117	201	3/13/69
	BK						

Foreign Patent Documents

							Translation	
		Document Number	Date	Country	Class	Subclass	Yes	No
	BL							
	BM							
	BN							
	BO							
	BP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	BR	Nguyen, S. et al., "Reaction Mechanisms of Plasma- and Thermal-Assisted Chemical Vapor Deposition of Tetraethylorthosilicate Oxide Films", <u>J. Electrochem. Soc.</u> , Vol. 137, No. 7, July, 1990, pp. 2209-2215.
	BS	Peters, Laura, "Low-k Dielectrics: Will Spin-On or CVD Prevail?", <u>Semiconductor International</u> , Vol. 23, No. 6, June, 2000, pp. 108-110, 114, 116, 118, 122, and 124.
	BT	Peters, Laura, "Pursuing the Perfect Low-k Dielectric", <u>Semiconductor International</u> , Vol. 21, No. 10, September, 1998, pp. 64-66, 68, 70, 72, and 74.

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U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	CA	6,153,524	11/28/00	Henley et al.	438	691	7/28/98
	CB	6,051,073	4/18/00	Chu et al.	118	723	6/3/98
	CC	5,580,429	12/3/96	Chan et al.	204	192.38	6/7/95
	CD	5,558,718	9/24/96	Leung	118	723E	4/8/94
	CE	5,628,871	5/13/97	Shinagawa	438	514	6/24/94
	CF	6,204,192	3/20/01	Zhao et al.	438	723	3/29/99
	CG	6,232,658	5/15/01	Catabay et al.	257	701	6/30/99
	CH	6,037,248	3/14/00	Ahn	438	619	6/13/97
	CI	5,675,187	10/7/97	Numata et al.	257	758	5/16/96
	CJ	5,559,367	9/24/96	Cohen et al.	257	77	7/12/94
	CK	5,376,595	12/27/94	Zupancic et al.	501	12	8/28/92

Foreign Patent Documents

							Translation	
		Document Number	Date	Country	Class	Subclass	Yes	No
	CL	2000-267128	9/29/00	Japan	G02F	1/136	X-Abstract Only	
	CM							
	CN							
	CO							
	CP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	CR	Sugahara, Satoshi, et al., "Chemical Vapor Deposition of CF ₃ -Incorporated Silica Films for Interlayer Dielectric Application", 1999 Joint International Meeting, <u>Electrochemical Society Meeting Abstracts</u> , Vol. 99-2, 1999, Abstract No. 746.
	CS	Koda, Seiichiro, et al., "A Study of Inhibition Effects for Silane Combustion by Additive Gases", <u>Combustion and Flame</u> , Vol. 73, No. 2, August, 1988, pp. 187-194.
	CT	

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	00-643	
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	Sheldon Aronowitz et al.	
Filing Date Herewith	Group Unknown	

U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	DA	5,904,154	5/18/99	Chien et al.	134	1.2	7/24/97
	DB	5,882,489	3/16/99	Bersin et al.	204	192.35	4/26/96
	DC	5,858,879	1/12/99	Chao et al.	438	725	6/6/97
	DD	3,012,861	12/12/61	Ling	23	223.5	1/15/60
	DE	3,178,392	4/13/65	Kriner	260	46.5	4/9/62
	DF	3,832,202	8/27/74	Ritchie	106	287	8/8/72
	DG	3,920,865	11/18/75	Läuffer et al.	427	220	4/6/72
	DH	4,705,725	11/10/87	Glaich et al.	428	405	11/28/86
	DI	5,194,333	3/16/93	Ohnaka et al.	428	405	12/18/90
	DJ	5,874,745	2/23/99	Kuo	257	59	8/5/97
	DK						

Foreign Patent Documents								
Translation								
		Document Number	Date	Country	Class	Subclass	Yes	No
	DL	DE 198 04 375 A1	7/1/99	Germany	H 01 L	21/312		X
	DM	EP 0 706 216 A2	4/10/96	Europe	H 01 L	23/532	N/A	
	DN	EP 0 949 663 A2	10/13/99	Europe	H 01 L	21/312	N/A	
	DO	63003437	1/8/88	Japan	H 01 L	21/90	X-Abstract Only	
	DP	WO 99/41423	8/19/99	PCT	C 23 C		N/A	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
	DR	
	DS	
	DT	

Examiner	Date Considered
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